

# **MB508**

# 2.3GHz TWO MODULUS PRESCALER

#### 2.3GHz TWO MODULUS PRESCALER

The Fujitsu MB508 is a 2.3GHz two modulus prescaler used with a frequency synthesizer to form a Phase Locked Loop (PLL) and divides the input frequency by a modulus of 128/130, 256/258 or 512/514. The output level is 1.6V peak to peak ECL level. The ultra high frequency operation provides wide application, such as Direct Broadcasting Satellite System, CATV system, UHF Transceiver, etc.

#### **FEATURES**

High Frequency Operation: f = 2.3GHz max. (P<sub>IN</sub> = -4dBm min.)

• Input Signal Amplitude:  $V_{IN} = 100 \text{mV}_{D-D}$  ( $f_{IN} = 100 \text{MHz}$  to 1.8GHz)

Pulse Swallow Function: 128/130, 256/258, 512/514

Power Dissipation: 120mW typ.

Wide Operation Temperature: -40°C to +85°C

• Stable Output Amplitude:  $V_{OUT} = 1.6V_{p-p}$  typ.

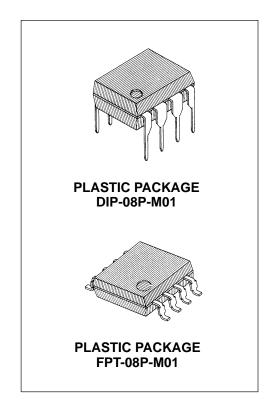
 Complete PLL synthesizer circuit with the Fujitsu MB87001A, PLL synthesizer system block IC

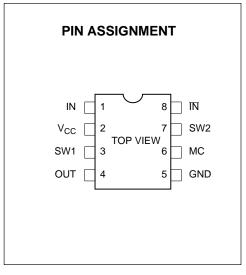
• Standard Plastic 8-pin Dual-In-Line Package or Flat Package

### **ABSOLUTE MAXIMUM RATINGS (See Note)**

Rating	Symbol	Value	Unit
Power Supply Voltage	V <sub>CC</sub>	-0.5 to +7.0	V
Input Voltage	V <sub>IN</sub>	–0.5 to V <sub>CC</sub>	V
Output Current	Io	10	mA
Operating Temperature	T <sub>A</sub>	-40 to +85	°C
Storage Temperature	T <sub>STG</sub>	-55 to +125	°C

Note: Permanent device damage may occur if the above Absolute Maximum Ratings are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

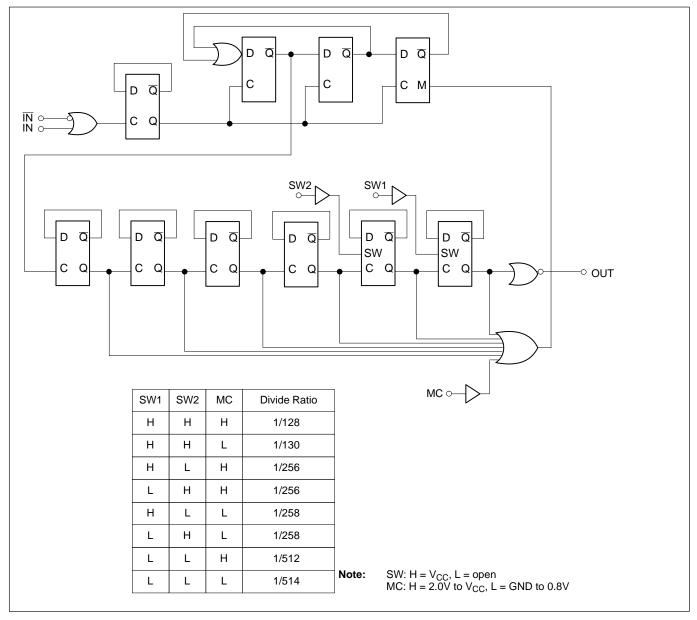


Figure 1. MB508 Block Diagram

# **PIN DESCRIPTION**

Pin Number	Symbol	Descriptions
1	IN	Input
2	V <sub>CC</sub>	Power Supply, +5V
3	SW1	Divide Ratio Control Input (See Divide Ratio Table)
4	OUT	Output
5	GND	Ground
6	MC	Modulus Control Input (See Divide Ratio Table)
7	SW2	Divide Ratio Control Input (See Divide Ratio Table)
8	ĪN	Complementary Input

# **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Values			Unit
Parameter	Symbol	Min.	Тур.	Max.	Oilit
Power Supply Voltage	V <sub>CC</sub>	4.5	5.0	5.5	V
Output Current	I <sub>O</sub>		1.2		mA
Operating Temperature	T <sub>A</sub>	-40		+85	°C
Load Capacitance	C <sub>L</sub>			12	pF

# **ELECTRICAL CHARACTERISTICS**

(Recommended Operating Conditions unless otherwise noted.)

Parameter	Symbol	Condition	Values			
			Min.	Тур.	Max.	Unit
Power Supply Current	I <sub>CC</sub>			24		mA
Output Amplitude	Vo		1.0	1.6		V <sub>p-p</sub>
Input Frequency	f <sub>IN</sub>	with input coupling capacitor 1000pF	100		2300	MHz
Input Signal Amplitude	P <sub>INA</sub>	f <sub>IN</sub> = 1800MHz to 2300MHz	-4		5.5	dBm
	P <sub>INB</sub>	f <sub>IN</sub> = 100MHz to 1800MHz	-16		10	
High Level Input Voltage for MC	V <sub>IHM</sub>		2.0			V
Low Level Input Voltage for MC	V <sub>ILM</sub>				0.8	V
High Level Input Voltage for SW	V <sub>IHS</sub> *		V <sub>CC</sub> -0.1	V <sub>CC</sub>	V <sub>CC</sub> +0.1	V
Low Level Input Voltage for SW	V <sub>ILS</sub>			Open	•	V
High Level Input Current for MC	I <sub>IHM</sub>	V <sub>IH</sub> = 2.0V			0.4	mA
Low Level Input Current for MC	I <sub>ILM</sub>	V <sub>IL</sub> = 0.8V	-0.2			mA
High Level Input Current for SW	I <sub>IHS</sub>	V <sub>IH</sub> = V <sub>CC</sub>			250	μΑ
Modulus Set-up Time MC to Output at 2.3GHz Operation	t <sub>SET</sub>			18	28	ns

Note: \*Design Guarantee

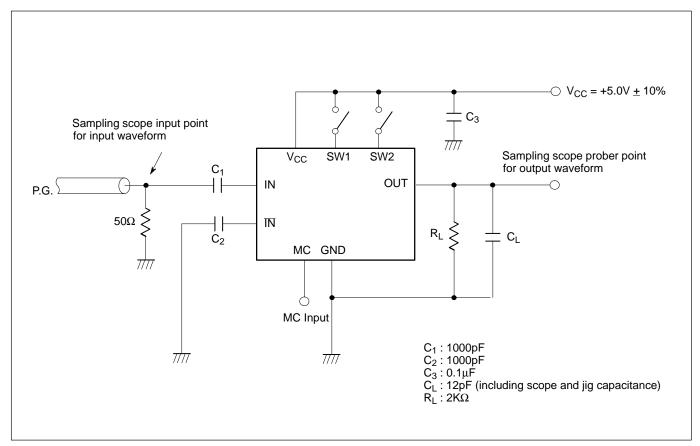
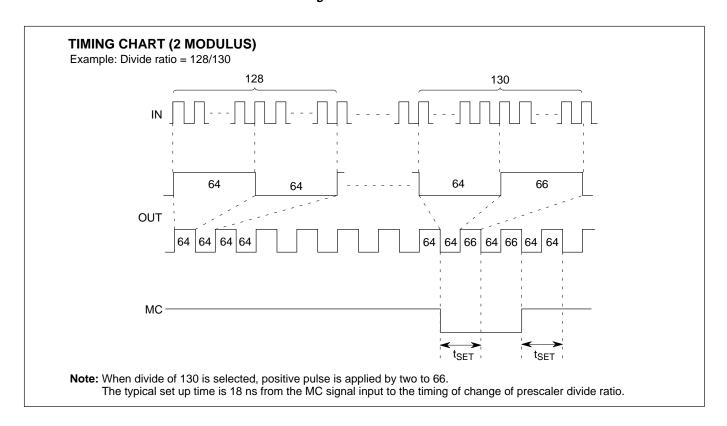


Figure 2. Test Circuit



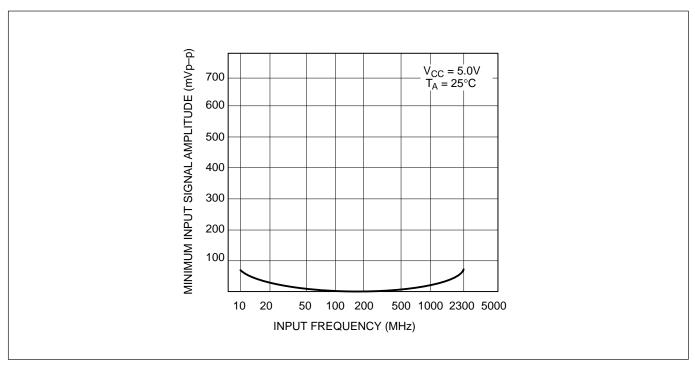


Figure 3. Input Signal Amplitude vs. Input Frequency

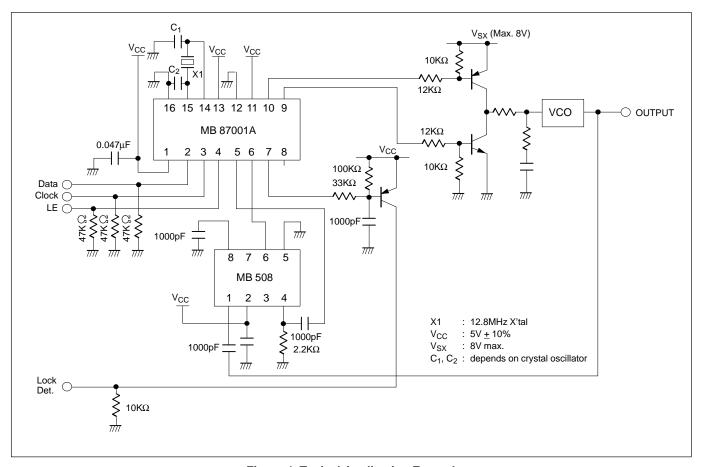
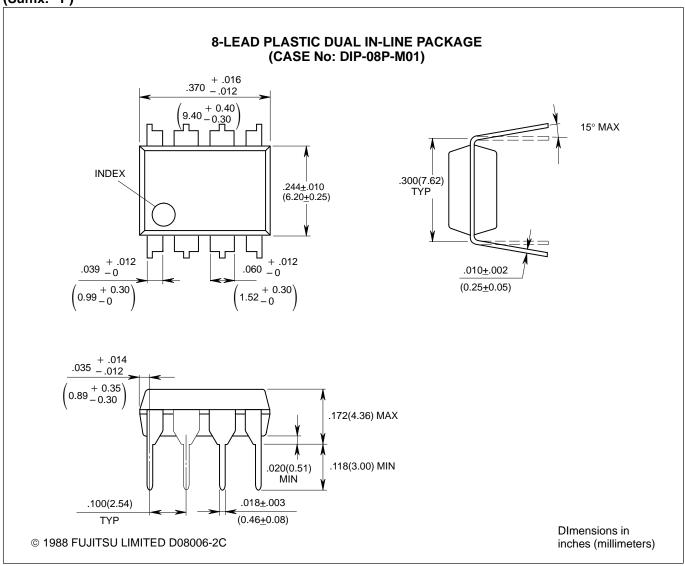


Figure 4. Typical Application Example

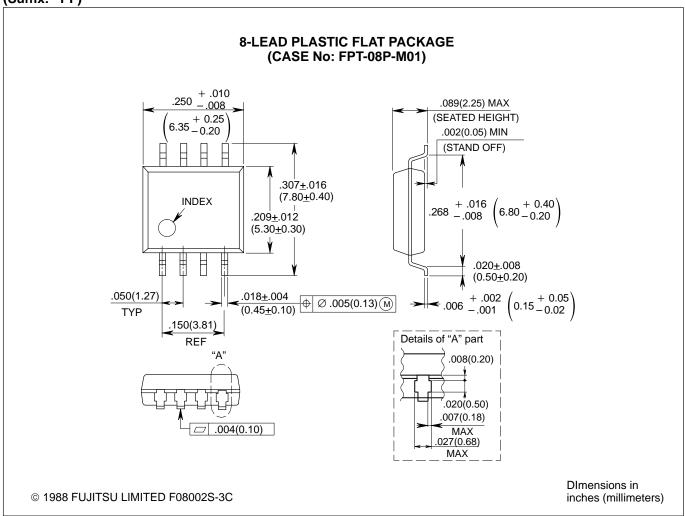
# **PACKAGE DIMENSIONS**

(Suffix: -P)



# **PACKAGE DIMENSIONS** (Continued)

(Suffix: -PF)



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# **FUJITSU LIMITED**

For further information please contact:

### Japan

**FUJITSU LIMITED** International Marketing Div. Furukawa Sogo Bldg., 6-1, Marunouchi 2-chome Chiyoda-ku, Tokyo 100, Japan Tel: (03) 3216-3211 Telex: 781-2224361 FAX: (03) 3215-0662

### **North and South America**

FUJITSU MICROELECTRONICS, INC. Semiconductor Division 3545 North First Street San Jose, CA 95134-1804, USA Tel: 408-922-9000 FAX: 408-432-9044

### **Europe**

FUJITSU MIKROELEKTRONIK GmbH Am Siebenstein 6-10, 6072 Dreieich-Buchschlag, Germany Tel: (06103) 690-0 Telex: 411963

FAX: (06103) 690-122

### Asia

FUJITSU MICROELECTRONICS ASIA PTE LIMITED 51 Bras Basah Road, Plaza By The Park, #06-04 to #06-07 Singapore 0719 Tel: 336-1600

Telex: 55573 FAX: 336-1609